ODSA
Enabling Heterogenous Integration

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OCP Global Forum 2020
ODSA Workgroup

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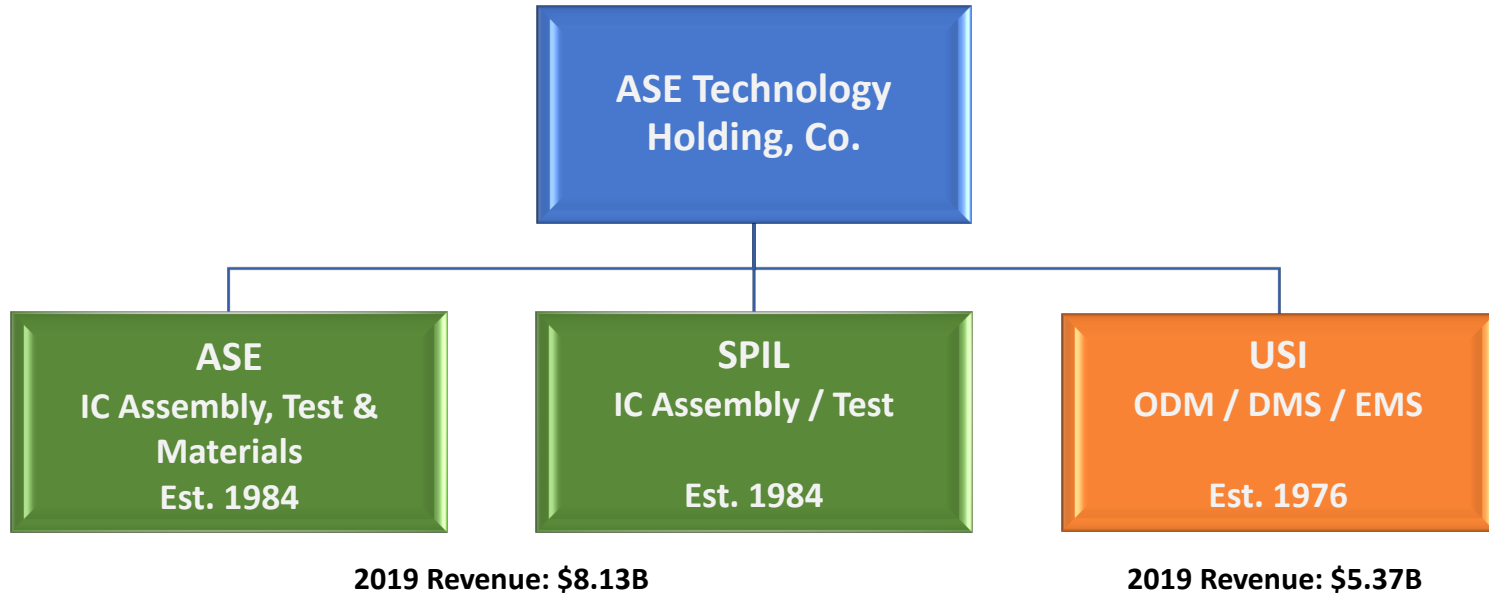ASE GROUP

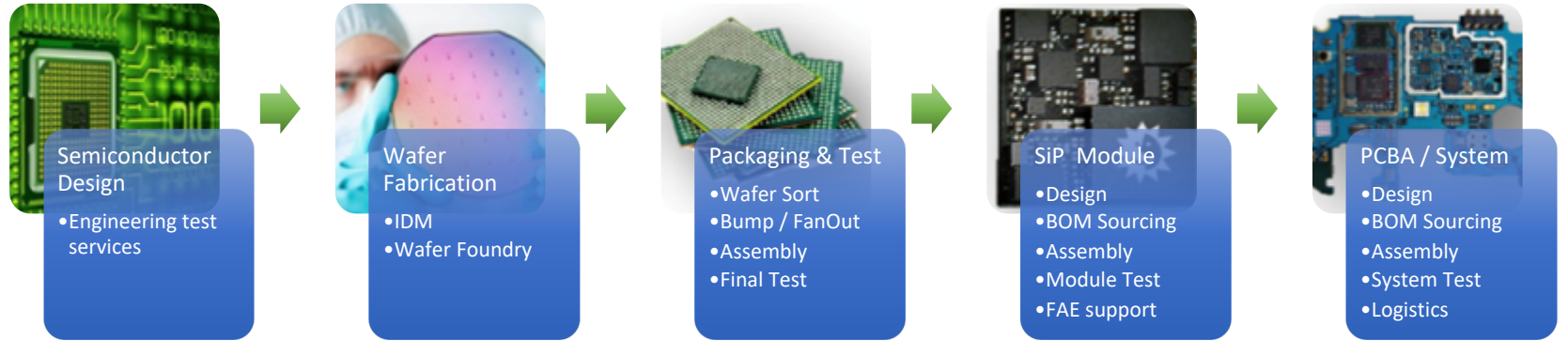# ASE Introduction

Organization

```
                    ASE Technology
                     Holding, Co.
```

ASE	SPIL	USI
IC Assembly, Test & Materials	IC Assembly / Test	ODM / DMS / EMS
Est. 1984	Est. 1984	Est. 1976

2019 Revenue: $8.13B   **2019 Revenue: $5.37B**

Providing Complete Value Chain Solution

Integrating OSAT and EMS

Semiconductor Design
- Engineering test services

Wafer Fabrication
- IDM
- Wafer Foundry

Packaging & Test
- Wafer Sort
- Bump / FanOut
- Assembly
- Final Test

SiP Module
- Design
- BOM Sourcing
- Assembly
- Module Test
- FAE support

PCBA / System
- Design
- BOM Sourcing
- Assembly
- System Test
- Logistics

ASE Group Services

ASE GROUP

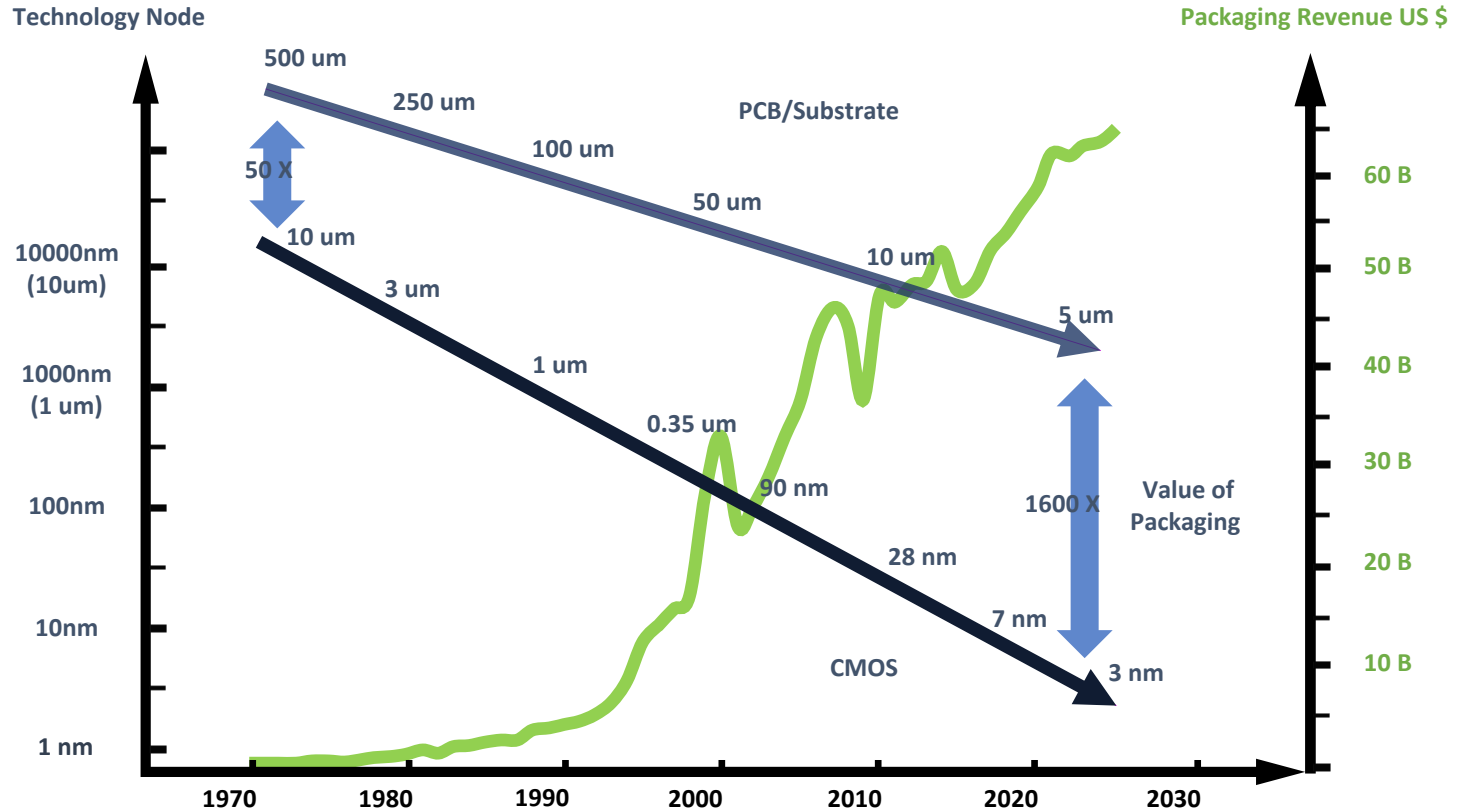# Packaging Market Drivers

Semiconductor Revenue vs. Process Generation
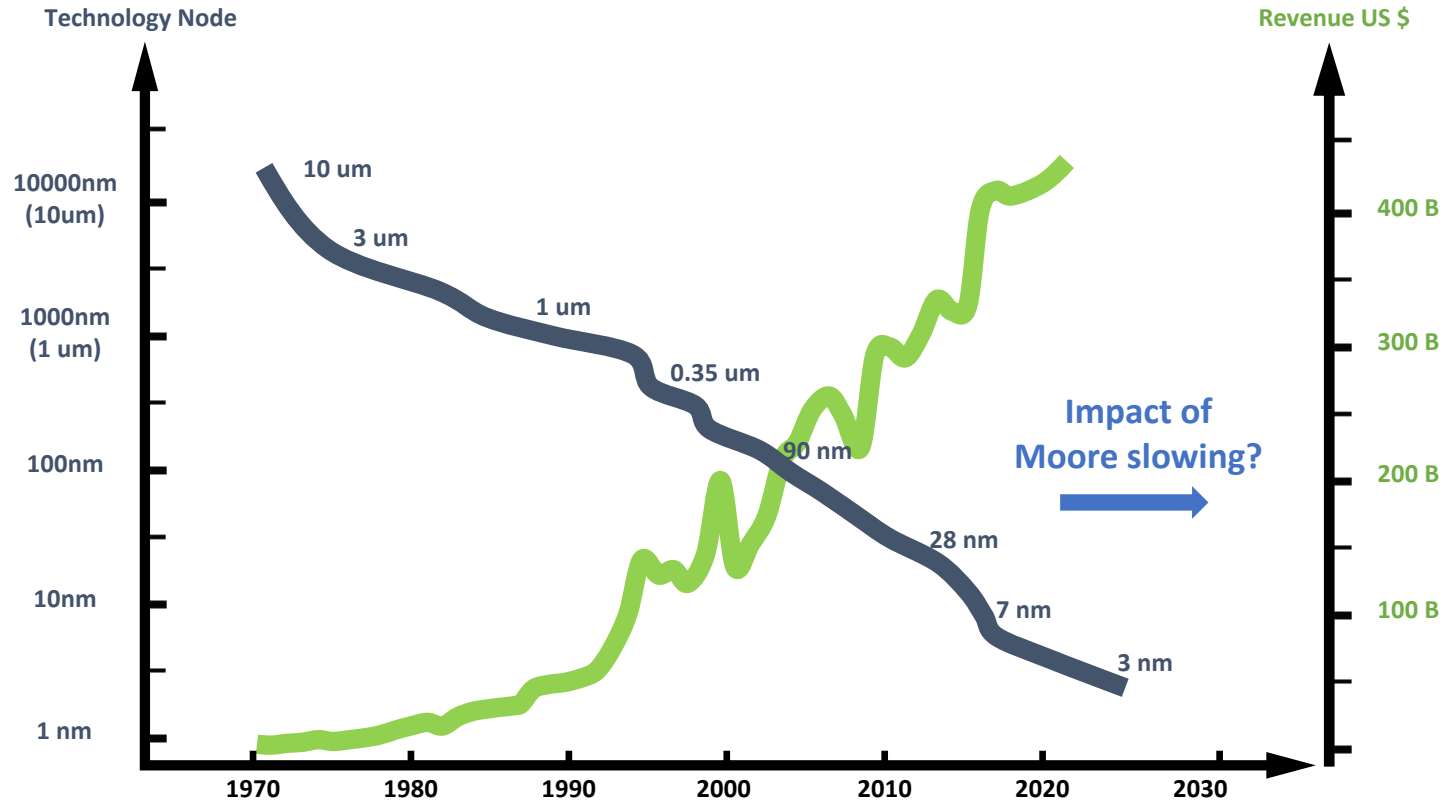
Value of Semiconductor Packaging is Increasing

Technology Node

Packaging Revenue US $

500 um

250 um

PCB/Substrate

100 um

50 um

50 X

10 um

10 um

10000nm
(10um)

3 um

5 um

1 um

1000nm
(1 um)

0.35 um

100nm

90 nm

1600 X

Value of
Packaging

10nm

28 nm

7 nm

CMOS

3 nm

1 nm

1970   1980   1990   2000   2010   2020   2030

60 B

50 B

40 B

30 B

20 B

10 B

Chip & System Integration Convergence

Technology Node

- 10 um — DIP
- 3 um — QFP
- 1 um
- 0.8 um — BGA
- 0.35 um — FC BGA
- 90 nm — SiP
- 28 nm
- 16 nm
- 7 nm
- 3 nm

Package Integration

SOC : Chip Integration

1970   1980   1990   2000   2010   2020   2030

Complexity

System Integration

Heterogeneous Integration
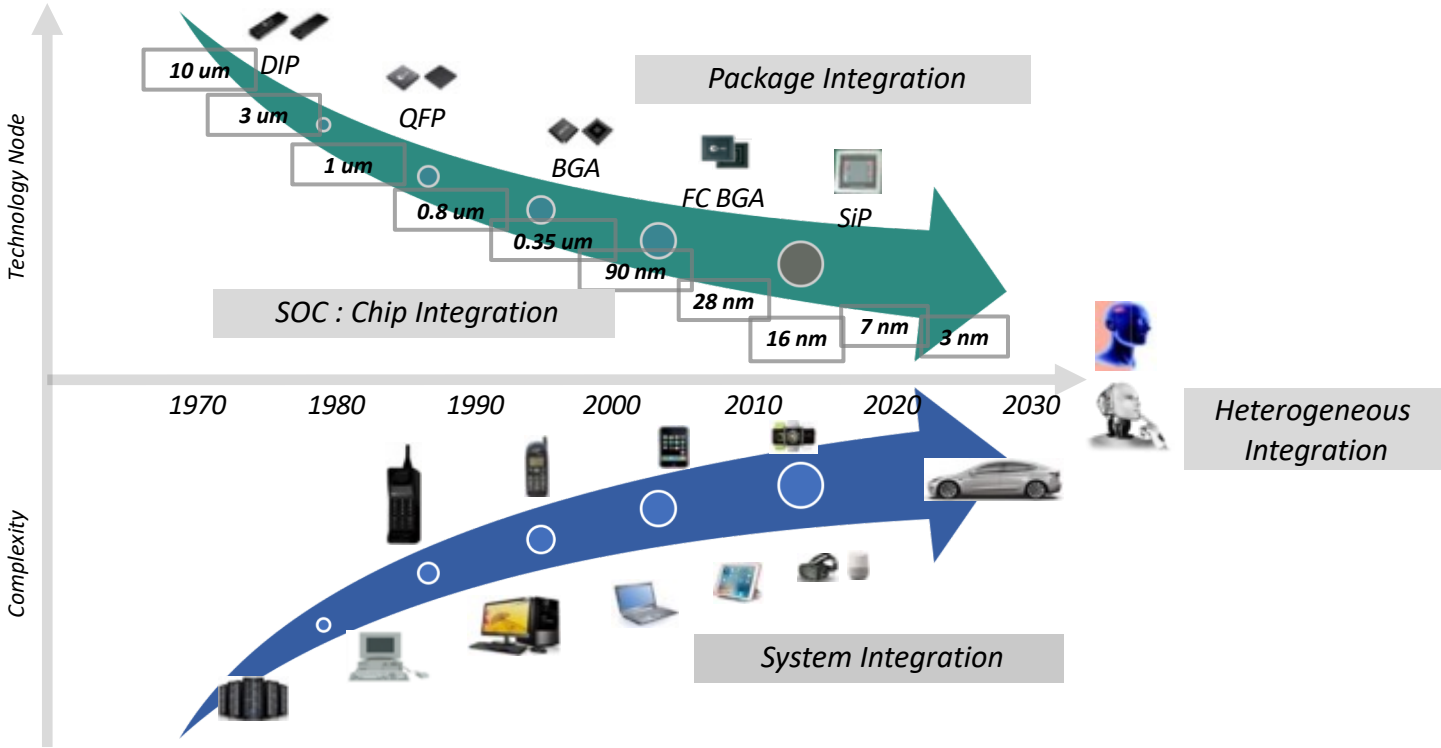
Silicon Integration Packaging Solutions

Silicon Integration Solutions

SiP	Flip Chip MCM	FanOut/RDL	2.5D TSV	3D IC

Development
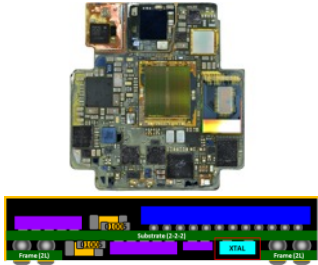
| SiP	Flip Chip MCM	FanOut/RDL	2.5D TSV	3D IC
• PCB/Substrate interconnect • Low/med density D2D • > 25um line/space • > 200um bump pitch • > 50um comp spacing • Bare/packaged parts • Chip last process	• Substrate interconnect • Low/med density D2D • > 10um line/space • > 125um bump pitch • > 50um D2D spacing • Chip last process	• RDL interconnect • Med/high density D2D • > 1um line/space • > 40um bump pitch • 100um D2D spacing • Chip first/last • FC to organic subs. • No TSV – lower loss	• Si interconnect • High density D2D • < 0.5um line/space • > 40um bump pitch • > 50um D2D spacing • Chip first/last • High bandwidth • Added Si layer • Power limited	• Si interconnect • High density D2D • Foundry line/space • < 10um bump pitch • High bandwidth • Shortest interconnect • Direct or hybrid bond • Custom die designs
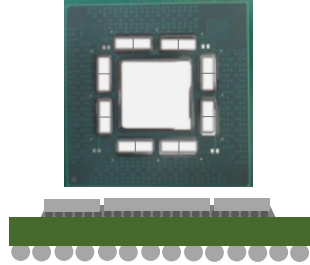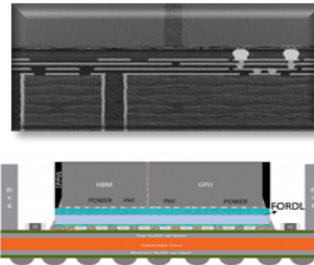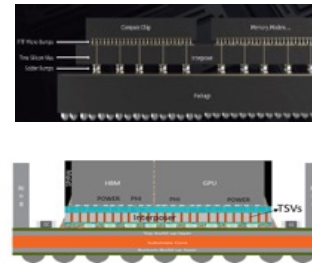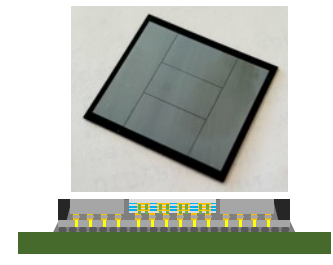
**Increasing Bandwidth & Cost** →

Flip Chip / MCM

- **Substrate based interconnect, > 10/10um line/space**
- **Multi-layer routing – 2/4 lyr core with build up layers**
- **Low to medium interconnect density (100's to 1,000)**
- **Package size: < 80x80mm (prod), < 120x120mm (dev)**
- **D2D spacing capability: 60um**
- **Benefits**
  - **Supports homo/heterogenous die partitioning**
  - **Enables IP reuse with advanced wafer node devices**
  - **Reduced SoC design and validation time**
  - **Enable multiple sources for 'standard' IP blocks / devices**
  - **Smaller SoC die size – increased yield**
  - **Lower bump/die stress – increased reliability**
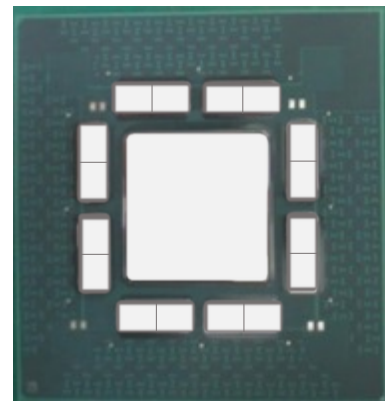
SoC + 16 chiplets
60um die to die spacing min

FanOut / FOCoS

- **RDL based interconnect, 2/2um line/space**
- **Multi-layer routing (3-4 lyrs.)**
- **Medium to high interconnect density (1000's to 10,000)**
- **Large FO area (1200-1600mm2)**
- **Stacked vias (10um hole/15um land)**
- **Chip first or chip last process**
- **Benefits**
  - **Die size, yield and cost optimization**
  - **Process node / functionality optimization**
  - **Integration of digital/analog SoCs**
  - **Short, high density interconnect**
  - **No TSV - Lower cost alternative to 2.5D**
  - **Increased reliability vs. MCM**

28nm   16nm

Fan Out Compound Die
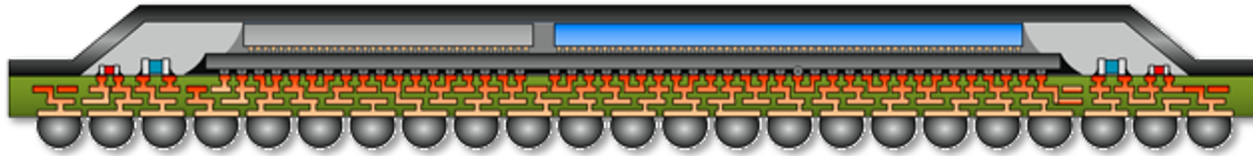
Fan Out Hybrid BGA Package
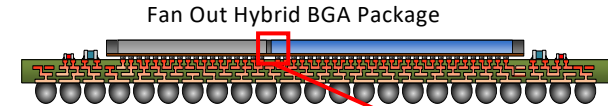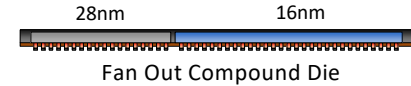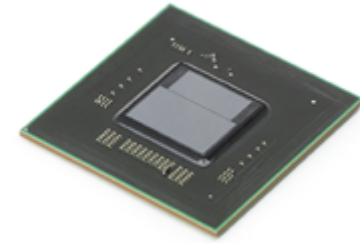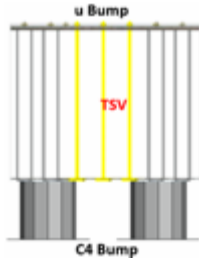
Stacked Via

2/2 µm Lines/Spaces
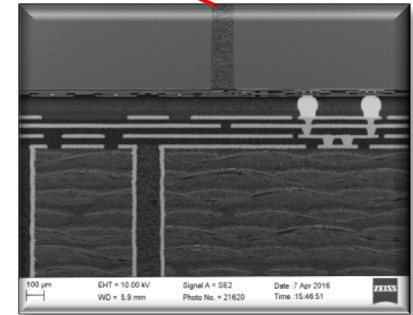
FOCoS Chip First Production Cross Sections
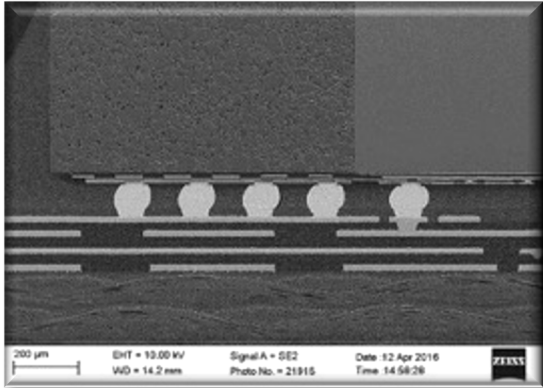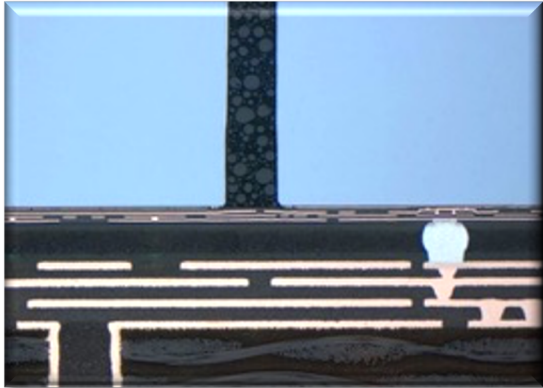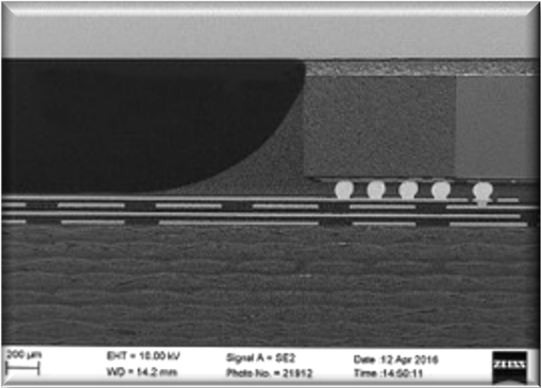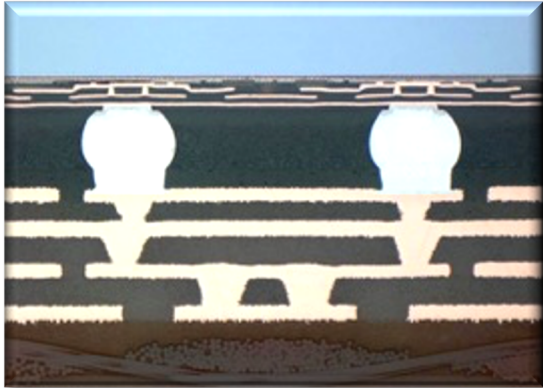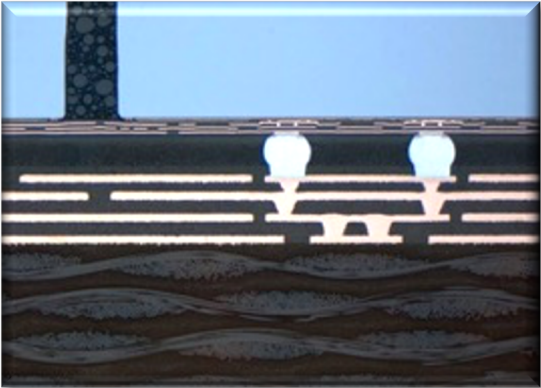
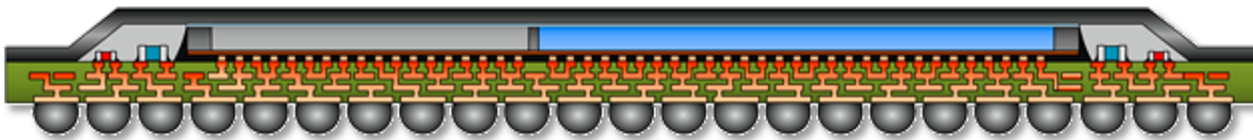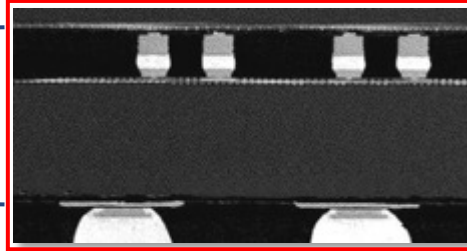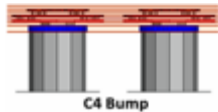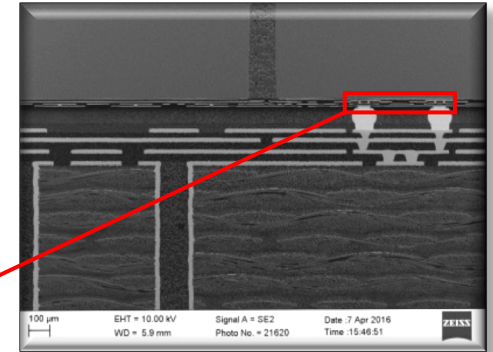# 2.5D TSV Replacement Opportunity

2.5D Interposer Package
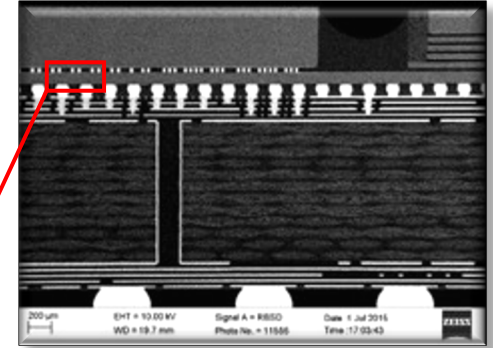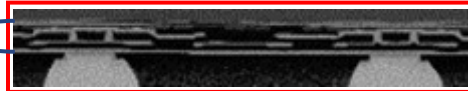
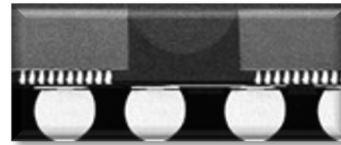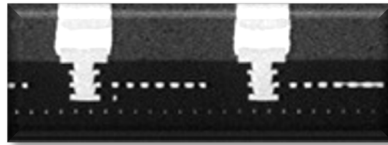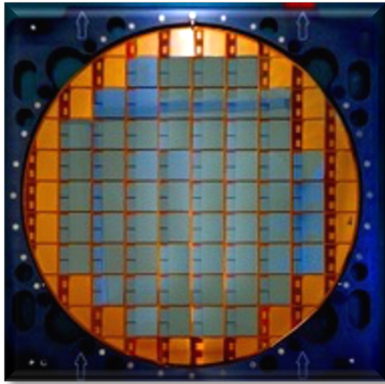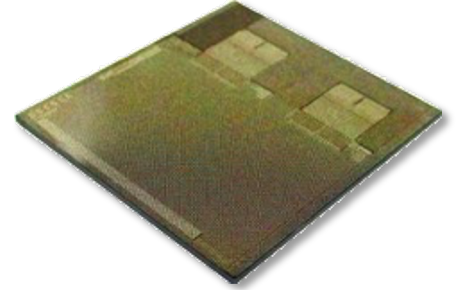**3D Interposer Interconnection**

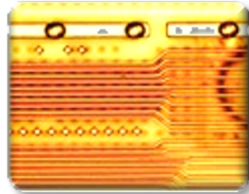**Fan Out Chip on Substrate 2.xD Package**

3D Fan Out Interconnection

ASE GROUP

FOCoS Chip Last With HBM

- **Chip Last Construction**
- **3,496 RDL traces to HBMs**
- **>15,500 C4 Bumps on Fan Out Composite Die**
- **6 Metal Layers**
  - **4 RDL layers**
  - **2 layers with 2µm/2µm L/S**
  - **1 UBM Layer**
  - **1 C4 Layer**
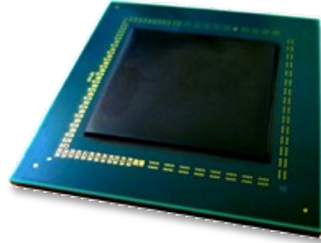
2.5D TSV

- **Silicon based interconnect, < 0.5/0.5um line/space**
- **High interconnect density (10,000's to 100,000)**
- **> 40um microbump pitch**
- **Supports:**
  - **Die partitioning**
  - **Memory integration**
  - **Optics integration (optical bench)**
- **Benefits**
  - **Silicon interconnect performance**
  - **High bandwidth interface enablement**
  - **Reduced power**
  - **Si on Si first level interconnect**
  - **System board size reduction**

HBM2 stack   SoC   HBM2 stack
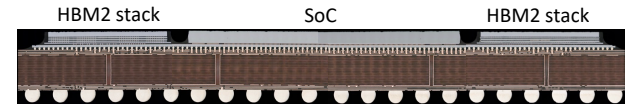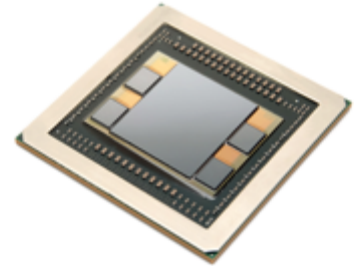
ASE - ODSA Engagement Objectives

- **Respond to increased need for heterogeneous die integration**
  - **Disaggregation of complex die**
  - **Shrink system board into package**
- **Drive cost reduction & scaling**
  - **Reduce design & development time**
  - **Decrease customization**
  - **Engage supply chain**
- **Enable mass adoption**
  - **Develop package level interface design guidelines**
  - **Establish interface design libraries**
  - **Enable design & simulation tool integration**
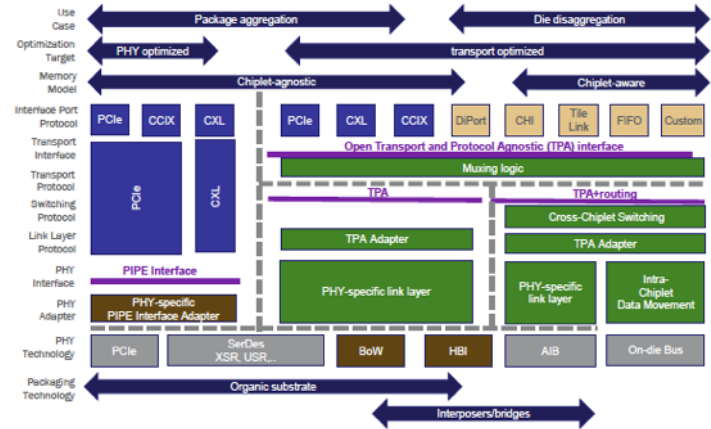
Open interface for chiplet communication

Next Steps / Call to Action

- **Establish working group under/as part of ODSA CDX to focus on package interface design rules & layout**

- **Members to include:**
  - **ODSA BoW & OpenHBI interface architecture developers**
  - **Other / 3rd party interface architecture developers (AIB, XSR/USR, etc.)**
  - **EDA tool & library suppliers**
  - **Package substrate design/simulation service providers (OSAT and/or independent)**

- **Assess feasibility of establishing physical interface layout / pin out standards (eg. DDRx, HBM, AIB)**

- **Identify critical interface layout requirements and develop 'PRD' specification per interface**

- **Establish design guidelines and develop interface design libraries**
  - **Organic substrate interconnect (> 10um line/space)**
  - **Redistribution layer interconnect (> 1um line/space)**
  - **Silicon substrate (2.5D) interconnect (< 0.5um line/space)**

- **Demonstrate virtual chiplet integration design flow**
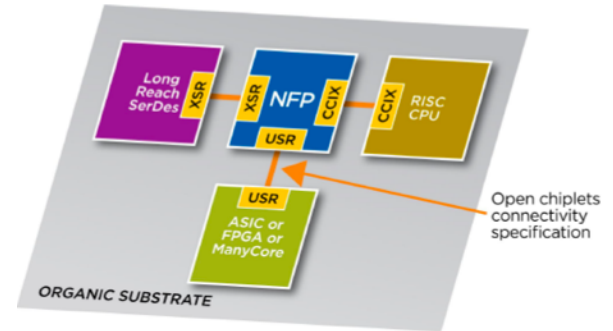
Thank You

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